New Jersey Semi-Conductor Products, Inc.

20 STERN AVE.
SPRINGFIELD, NEW JERSEY 07081
U.S.A.

TELEPHONE: (973) 376-2922
(212) 227-6005
FAX: (973) 376-8960

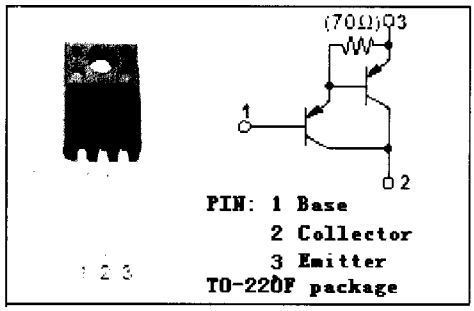
Silicon PNP Darlington Power Transistor 2SB1626

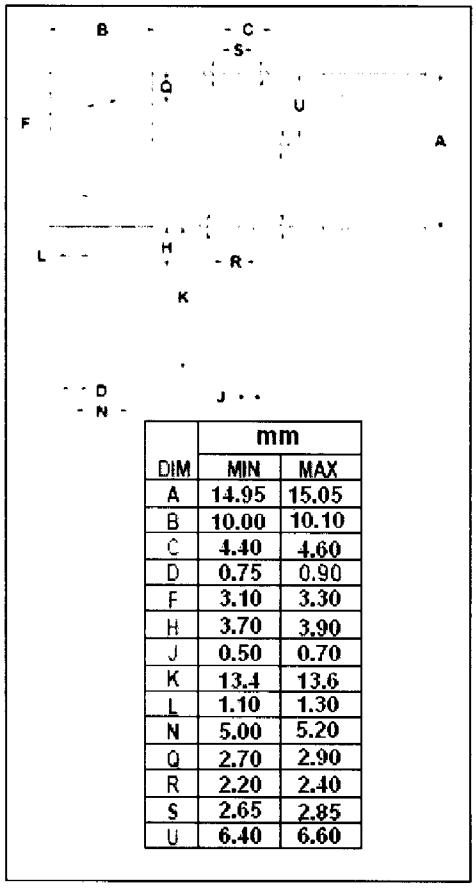
DESCRIPTION

- High DC Current Gain
- Low-Collector Saturation Voltage
- Complement to Type 2SD2495

APPLICATIONS

- Designed for audio,series regulator and general purpose applications.





DIM	mm MIN	MAX
A	14.95	15.05
B	10.00	10.10
C	4.40	4.60
D	0.75	0.90
F	3.10	3.30
H	3.70	3.90
J	0.50	0.70
K	13.4	13.6
L	1.10	1.30
N	5.00	5.20
Q	2.70	2.90
R	2.20	2.40
S	2.65	2.85
U	6.40	6.60

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	-110	V
V_{CEO}	Collector-Emitter Voltage	-110	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current-Continuous	-6	A
I_B	Base Current- Continuous	-1	A
P_C	Collector Power Dissipation @ T_C=25℃	30	W
T_J	Junction Temperature	150	℃
T_{stg}	Storage Temperature Range	-55~150	℃

NJ Semi-Conductors reserves the right to change test conditions, parameter limits and package dimensions without notice. Information furnished by NJ Semi-Conductors is believed to be both accurate and reliable at the time of going to press. However, NJ Semi-Conductors assumes no responsibility for any errors or omissions discovered in its use. NJ Semi-Conductors encourages customers to verify that datasheets are current before placing orders.

Quality Semi-Conductors

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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	I_C= -30mA; I_B= 0	-110			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	I_C= -5A; I_B= -5mA			-2.5	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	I_C= -5A; I_B= -5mA			-3.0	V
I_{CBO}	Collector Cutoff Current	V_{CB}= -110V; I_E= 0			-100	μ A
I_{EBO}	Emitter Cutoff Current	V_{EB}= -5V; I_C= 0			-100	μ A
h_{FE}	DC Current Gain	I_C= -5A; V_{CE}= -4V	5000		30000	
C_{OB}	Collector Output Capacitance	I_E= 0; V_{CB}= -10V; f= 1MHz		110		pF
f_T	Current-Gain—Bandwidth Product	I_E= 0.5A; V_{CE}= -12V		100		MHz

◆ **h_{FE} Classifications**

O	P	Y
5000-12000	6500-20000	15000-30000

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